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Customer No.: 31561
Docket No.: 13184-US-PA
Application No.: 10/710,696

after attaching a dielectric substrate over the device on the surface of the wafer, grinding the surface of the dielectric substrate away from the wafer or the surface of the wafer away from the dielectric substrate.

11. (original) The device grinding process of claim 10, wherein the device comprises a photoelectric device.
12. (original) The device grinding process of claim 11, wherein the photoelectric device comprises an image sensor.
13. (original) The device grinding process of claim 11, wherein each photoelectric device has a micro-mechanical structure.
14. (original) The device grinding process of claim 13, wherein the micro-mechanical structure protrudes from the surface of the wafer by a height smaller than the gap between the dielectric substrate and the wafer.

15-16. (canceled)

17. (previously presented) The device grinding process of claim 10, wherein the material constituting the spacers comprises silicon oxide.

18. (previously presented) The device grinding process of claim 10, wherein the material constituting the glue is selected from a group consisting of ultraviolet cured plastic and epoxy resin.

19. (original) The device grinding process of claim 10, wherein the step of grinding

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the dielectric substrate or the wafer comprises mechanical grinding.

20. (original) The device grinding process of claim 10, wherein the dielectric substrate comprises a glass substrate or a silicon substrate.

21. (original) The device grinding process of claim 10, wherein the chip unit and the dielectric substrate together form at least a sealed chamber such that the device is enclosed within the sealed chamber.